

In the Claims:

Please amend the claims as follows.

1. (currently amended) A phase shift photomask, comprising:
a transparent substrate;
at least one isolated linear pattern on the substrate, including a transparent end portion with a phase shift of 180° relative to the substrate;
a plurality of dense linear patterns on the substrate; and
a transparent phase-shift region, located on the substrate adjacent to ends of the dense linear patterns and having a phase shift of 90° relative to the substrate,
wherein no phase shift region is present between any two neighboring dense linear patterns that are arranged in a direction different from an extending direction of each dense linear pattern.
2. (original) The phase shift photomask of claim 1, wherein the substrate comprises quartz or glass.
3. (previously presented) The phase shift photomask of claim 1, wherein the dense linear patterns and the isolated linear pattern except its transparent end portion each comprise an opaque linear layer.
4. (previously presented) The phase shift photomask of claim 1, wherein the dense linear patterns and the isolated linear pattern except its transparent end portion each comprise a semi-transparent linear layer with a phase shift of 180° relative to the substrate.
5. (previously presented) The phase shift photomask of claim 1, wherein the transparent end portion of the isolated linear pattern and the transparent phase-shift region each comprise a recessed portion of the substrate.
6. (original) The phase shift photomask of claim 1, including a pair of opposite

isolated linear patterns with their transparent end portions facing each other.

7. (original) The phase shift photomask of claim 1, wherein the dense linear patterns include two groups of dense linear patterns separated by the transparent phase-shift region, wherein the ends of the dense linear patterns in each group are adjacent to the transparent phase-shift region.

8. (currently amended) A phase shift photomask, comprising:

a transparent substrate; and

an isolated linear pattern on the substrate, including a transparent end portion with a phase shift of 180° relative to the substrate ~~without a phase shift region adjacent to two sides thereof~~ and with a transparency equal to a transparency of the substrate around the isolated linear pattern, wherein the transparent end portion is disposed in a manner such that an end of an isolated linear photoresist pattern is defined by the isolated linear pattern in a lithography process, and a position of the end of the isolated linear photoresist pattern corresponds to is covered by a position of the transparent end portion in the lithography process.

9. (original) The phase shift photomask of claim 8, wherein the substrate comprises quartz or glass.

10. (original) The phase shift photomask of claim 8, wherein the isolated linear pattern except its transparent end portion comprises an opaque linear layer.

11. (original) The phase shift photomask of claim 8, wherein the isolated linear pattern except its transparent end portion comprises a semi-transparent linear layer with a phase shift of 180° relative to the substrate.

12. (original) The phase shift photomask of claim 8, wherein the transparent end portion of the isolated linear pattern comprises a recessed portion of the substrate.

13. (original) The phase shift photomask of claim 8, including a pair of opposite isolated linear patterns with their transparent end portions facing each other.

14. (currently amended) A phase shift photomask, comprising:

a transparent substrate;

a plurality of dense linear patterns on the substrate; and

a transparent phase-shift region, located on the substrate adjacent to ends of the dense linear patterns and having a phase shift of 90° relative to the substrate,

wherein no phase shift region is present between any two neighboring dense linear patterns that are arranged in a direction different from an extending direction of each dense linear pattern.

15. (original) The phase shift photomask of claim 14, wherein the substrate comprises quartz or glass.

16. (original) The phase shift photomask of claim 14, wherein the dense linear patterns comprise opaque linear layers.

17. (original) The phase shift photomask of claim 14, wherein the dense linear patterns comprise semi-transparent linear layers with a phase shift of 180° relative to the substrate.

18. (original) The phase shift photomask of claim 14, wherein the transparent phase-shift region comprises a recessed portion of the substrate.

19. (original) The phase shift photomask of claim 14, wherein the dense linear patterns include two groups of dense linear patterns separated by the transparent phase-shift region, wherein the ends of the dense linear patterns in each group are adjacent to the transparent phase-shift region.